Generation of Spin Defects by Ion Implantation in Hexagonal Boron Nitride

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Abstract: Optically addressable spin defects in wide-bandage semiconductors as promising systems for quantum information and sensing applications have attracted more and more attention recently. Spin defects in two-dimensional materials are supposed to have unique superiority in quantum sensing since their atomic thickness. Here, we demonstrate that the negatively boron charged vacancy ($V^-_B$) with good spin properties in hexagonal boron nitride can be generated by ion implantation. We carry out optically detected magnetic resonance measurements at room temperature to characterize the spin properties of $V^-_B$ defects, showing zero-field splitting of $\sim 3.47$ GHz. We compare the photoluminescence intensity and spin properties of $V^-_B$ defects generated by different implantation parameters, such as fluence, energy and ion species. With proper parameters, we can create $V^-_B$ defects successfully with high probability. Our results provide a simple and practicable method to create spin defects in hBN, which is of great significance for integrated hBN-based devices.

Keywords: 2D materials, hexagonal boron nitride, negatively boron charged vacancy, spin properties, ion implantation

Solid-state spin defects have attracted widespread attention as promising quantum systems in the last decades [1], and have numerous applications in quantum information [2,3] and quantum sensing [4-5]. Some prominent systems have been studied extensively, including the nitrogen-vacancy (NV) center [6,9] and the silicon-vacancy center [10,11] in diamond, the divacancy center [12,13] and the silicon-vacancy center [14,15] in silicon carbide, etc. Although these defects have many remarkable properties, such as long room-temperature spin coherence time [16], there are some intrinsic limitations due to the three-dimensional nature of the materials. For example, it is difficult to make the spin defects close to the sample surface, which affects the accuracy of the sensor [17].

Recently, the emergence of spin defects in two-dimensional materials and van der Waals crystals provides a remedy to the limitations of three-dimensional materials. One of the most outstanding materials is hexagonal boron nitride (hBN) that possesses a wide bandgap (hBN) which that a wide bandgap and a variety of atom-like defects, which makes hBN become a superb quantum system for single photon emitters [18,20] and spin-addressable systems at room temperature. Currently, one of the most researches on spin defects are about the negatively boron charged vacancy ($V^-_B$) that consists of a missing boron atom replaced by an extra electron in the hBN crystal [21-23]. The $V^-_B$ defects have great photostability and exhibit excellent spin properties at room temperature [24]. Besides, the $V^-_B$ defects have a triplet ground state ($S = 1$) and can be initialized, manipulated and optically read out at room temperature, showing the potential for spin-based quantum information and sensing applications [24-27].

In this context, we demonstrate a new way to generate $V^-_B$ defects in hBN crystal by ion implantation process using an ion implanter. At present, it is reported that the $V^-_B$ defects can be generated by high-dose neutron irradiation [24], focused ion beam (FIB) implantation [25] and femtosecond laser writing [26]. Compared with these approaches, ion implantation is more convenient to implement and the process is gentle and controllable. Moreover, the ion implanter is commercially available and has a variety of available ion sources [31]. With appropriate energy and fluence of implanted ions, we created $V^-_B$ defects successfully using an ion implanter, which exhibit good contrast in optically detected magnetic resonance (ODMR) results.

In the experiment, we used a commercially available monocrystalline hBN sample purchased from HQ Graphene with $\sim 1$ mm lateral size. The monocrystalline hBN was exfoliated with tape into 10-100 nm-thick flakes, which were transferred onto a silicon substrate later. The sample was then put into an ion implanter (IonImplantation-CETC-M56100) and the hBN flakes were implanted with parallelized ion beams over a large area. Through ion implantation process we created $V^-_B$ defects successfully. The process is schematically shown in Fig.1(a). The high-energy ions break the B-N bonds in the hBN lattice and knock out boron atoms, leaving negatively charged vacancies behind. The photoluminescence (PL) and spin properties of the defects

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are characterized by using a confocal microscope system combined with a microwave system. We use a 532-nm laser to excite the defects with laser power of 4.7 mW, a 0.5 N.A. objective (Olympus) to focus on the sample and collect the fluorescence by a 9-µm-core-diameter fiber to an avalanche photodiode, and a copper wire with a diameter of 20 µm that is close to the implanted sample as an antenna to deliver a microwave field.

With the setup described above, we first characterize the PL spectrum of the defects generated by implanting nitrogen ions with the energy of 30 keV and the fluence of \(1 \times 10^{14}\) ions/cm\(^2\), shown in Fig.1(c). The implanted samples exhibit strong PL emission ranging from 700 to 1000 nm and centered around 820 nm, which is the characteristic of \(V^\text{B}_\text{B}\) centers and consistent with reported \(V^\text{B}_\text{B}\) defects created by neutron irradiation, FIB and laser writing \[24, 25\]. Besides, the \(V^\text{B}_\text{B}\) defects that we create are stable for a long time at room temperature.

To further verify that the defects generated by ion implantation are \(V^\text{B}_\text{B}\) centers, we perform optically detected magnetic resonance (ODMR) measurements at room temperature. ODMR measurements are carried out by scanning the frequency of microwave filed from 3250 to 3750 MHz without external magnetic filed and the ODMR spectrum is fitted by two-Lorentzian function, shown in Fig.1(d). The result indicates that the fluorescence signal drops when the microwave filed oscillates at \(\nu_1 \sim 3405\) MHz and \(\nu_2 \sim 3548\) MHz, which is consistent with ODMR spectra of \(V^\text{B}_\text{B}\) defects measured in previous works \[24, 29\]. Fig.1(b) shows that the \(m_s = \pm 1\) excited state of \(V^\text{B}_\text{B}\) center is more likely to return \(m_s = 0\) ground state through the nonradiative intersystem crossing, so \(V^\text{B}_\text{B}\) spin will be polarized into \(m_s = 0\) ground state under continuous laser exciting. When the microwave frequency is in resonance with the splittings between ground state sublevels, photons in \(m_s = 0\) state will be pumped into \(m_s = \pm 1\) state, leading to a decrease in fluorescence intensity \[29\]. The \(V^\text{B}_\text{B}\) center has a triplet ground state \((S = 1)\) with a zero-field splitting (ZFS) described by the parameters \(D\) and \(E\). The resonance frequencies \(\nu_1\) and \(\nu_2\) in ODMR spectrum can be represented by \(\nu_{1,2} = D/h \pm \sqrt{E^2 + (g\mu_B B)^2}\), where \(h\) is the Planck constant, \(g\) is the Landé factor, \(\mu_B\) is the Bohr magneton and \(B\) is the static magnetic field \[24\]. In the absence of external magnetic filed, the ZFS parameters \(D\) and \(E\) can be given by \(D/h = (\nu_1 + \nu_2)/2\) and \(E/h = (\nu_2 - \nu_1)/2\). In our experiment, we find \(D/h = 3475 \pm 5\) MHz and \(E/h = 70 \pm 5\) MHz. These results show promising spin
properties of $V_{-B}$ defects generated by ion implantation.

Next, we study the effect of different implantation parameters, such as implantation fluence, energy and ion species. Firstly, we compare the implantation effect of different fluence. We generate defects by implanting nitrogen ions with the same energy (30 keV) and the increasing fluence from $1 \times 10^{13}$ to $1 \times 10^{16}$ ions/cm$^2$, respectively. Fig. 2(a) shows the comparison of four defect samples on PL spectra at room temperature. We find that the intensity of the PL spectra increases with increasing fluence at low doses. When the fluence is up to $1 \times 10^{14}$ ions/cm$^2$, the PL intensity is shown to decrease a little, which is similar to that observed in $V_{Si}$ defects in silicon carbide, NV and SiV centers in diamond [32–34]. The decrease can be considered as saturation phenomenon of the $V_{-B}$ defects generated by ion implantation, which might result from the ion-induced damage of the crystal lattices that accumulates in the form of multiple vacancy defects [32, 34]. The ODMR spectra with two-Lorentzian fitting at different fluence are shown in Fig. 2(b). The measurements are carried out without external magnetic filed at room temperature. We find that the ZFS parameter $D$ is stable at $\sim 3475$ MHz, while the ZFS parameter $E$ increases almost linearly with the fluence ranging from $1 \times 10^{13}$ to $1 \times 10^{15}$ ions/cm$^2$, shown in Fig. 2(c). The slope of the linear fitting curve is around 10 MHz/lg(ions/cm$^2$). However, when the fluence reaches to $1 \times 10^{16}$ ions/cm$^2$, the ZFS parameter $D$ is no longer stable and varies from 3460 to 3520 MHz, and $E$ is no longer linear. We conjecture that it is due to the lattice damage that influence the internal electron interactions.

Then, in order to compare the implantation effect of different energies, we generate defects by implanting nitrogen ions with the same fluence ($1 \times 10^{14}$ ions/cm$^2$) and varying energy from 20 keV to 40 keV, respectively. Fig. 3(a) shows the comparison of these defect samples on PL spectra and Fig. 3(b) shows the comparison on ODMR spectra at room temperature. We can see that different energies just affect the PL intensity but not the spin properties of the $V_{-B}$ defects. The PL spectrum of the $V_{-B}$ defects generated at 30-keV energy displays higher intensity than that of $V_{-B}$ defects generated at other energies, while the ODMR spectra of the $V_{-B}$ defects generated at different energies display the same resonance frequency, i.e., the same ZFS parameters $D$ and $E$.

Finally, to compare the implantation effect of different ion species, we generate defects by implanting nitro-
Fig. 3: Effects of the energy of the implanted nitrogen ions on the defects. The energy is varied from 20 keV to 40 keV. The implantation fluence is fixed at $1 \times 10^{14}$ ions/cm$^2$. (a) PL spectrum at room temperature of the defects created with different energies. (b) ODMR measurements without external magnetic filed of the defects created with different energies.

Fig. 4: Effects of different implanted ion species on the defects. The implantation fluence is fixed at $1 \times 10^{14}$ ions/cm$^2$ and the energy is fixed at 30 keV. (a) SRIM simulation of the defects’ distribution with depth generated by implanting different ions (He, C, N and Ar). (b) PL spectra at room temperature of the defects created with different ions. (c) ODMR measurements without external magnetic filed of the defects created with different ions. (d) The ZFS parameter $E$ varies with different ions.

gen, argon, helium and carbon ions with the same fluence ($1 \times 10^{14}$ ions/cm$^2$) and energy (30 keV), respectively. We simulate the theoretical distribution of the V$_B^-$ defects with depth created by different ions using Stopping-and-Range-of-Ions-in-Matter (SRIM) simulation, shown in Fig.4(a). The result indicates that the number of generated defects and the penetration depth are obviously different for different ions. Argon ions are more likely to create shallow defects, while helium ions can be used to create defects in thicker sample. Fig.4(b) shows the comparison of these samples on PL spectra at room temperature, from which we can see that the sample im-
planted using nitrogen ions has the highest PL intensity. Fig.4(c) shows the ODMR spectra of the defects generated by different implantation ions, indicating that they all have spin properties. We find that when we implant different ions, the ZFS parameter $D$ is stable at $\sim 3475$ MHz, while the ZFS parameter $E$ is different, which is similar to implantation with different fluence. The difference of the ZFS parameter $E$ is shown in Fig.4(d), showing that the ZFS parameter $E$ increases as the ions’ radius increases.

In conclusion, we have confirmed that we successfully generated the optically active $V_B$ defects by ion implantation in hBN. Our results show that the implantation parameters, such as fluence, energy and ion species, have clear effects on the PL intensity and spin properties of the ion-implantation-generated $V_B$ defects. Therefore, we can create good $V_B$ defects with high probability by adjusting the fluence ($1 \times 10^{14}$ ions/cm$^2$) and energy (30 keV) of the implanted nitrogen ions, and the $V_B$ defects exhibit a good ODMR contrast at room temperature, which is of great importance for spin-addressable systems. Our work provides a simple and practicable method for controllable engineering of spin defects in hBN and paves the way for integrated quantum information and sensing applications.

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[31] FIB has better positioning, but its often-used ion source is Ga. Other ion source is rare commerically.

